	Application No.	Applicant(s)	
Notice of Allowability	10/528,440	FUJIKAWA ET AL.	
	Examiner	Art Unit	
	Thao P. Le	2818	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED in is) or other appropriate common RIGHTS. This application is s	n this application. If not included unication will be mailed in due co	urse. THIS
1. This communication is responsive to <u>11/20/07</u> .			
2. X The allowed claim(s) is/are <u>1,6-8,10,11,25-27 and 29-34</u> .			
 3.		or (f).	
2. Certified copies of the priority documents hav		n No.	•
3. Copies of the certified copies of the priority do			n from the
International Bureau (PCT Rule 17.2(a)).		an mananan ataga appinasia.	
* Certified copies not received:			•
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 4. A SUBSTITUTE OATH OR DECLARATION must be submin INFORMAL PATENT APPLICATION (PTO-152) which give	MENT of this application. nitted. Note the attached EXA	AMINER'S AMENDMENT or NOT	
		deciaration is deficient.	
5. CORRECTED DRAWINGS (as "replacement sheets") mu		(575 648) # 1 1	
(a) including changes required by the Notice of Draftsper		v (PTO-948) attached	
1) hereto or 2) to Paper No./Mail Date			
(b) ☐ including changes required by the attached Examiner Paper No./Mail Date			
Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in	1.84(c)) should be written on the the header according to 37 CF	ne drawings in the front (not the ba R 1.121(d).	ck) of
 DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT 	osit of BIOLOGICAL MATE FOR THE DEPOSIT OF BIO	ERIAL must be submitted. Not DLOGICAL MATERIAL.	e the
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Attachment(s)			
1. Notice of References Cited (PTO-892)	5. Notice of In	formal Patent Application	
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. Interview Si	ummary (PTO-413),	
3. Information Disclosure Statements (PTO/SB/08),	Paper No./ 7. ⊠ Examiner's	Mail Date Amendment/Comment	
Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit	8. 🛭 Examiner's	Statement of Reasons for Allowa	nce
of Biological Material	9. Other	_•	•
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DETAILED ACTION

Examiner's Amendment

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Before "Technical field", please insert:

Cross-Reference To Related Application

This application is a 371 of PCT/JP04/05649 filed on 04/20/2004, which claims benefit of Japan application 2003-122240 filed on 04/25/2003, the contents of which are hereby incorporated herein by reference in their entirety.

Response to Amendment

This Office Action is in response to Amendment filed on 11/20/2007.

Claims 31-32 have been amended.

Claims 33-34 are newly added.

Claims 1, 6-8, 10-11, 25-27, 29-34 are pending.

Remark of Applicants has been considered.

Reason for allowance

Claims 1, 6-8, 10-11, 25-27, 29-34 are allowed. The following is an examiner's statement of reason for allowance:

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Claims 1, 6-8, 10-11, 25-26, 30-32: None of the references of record teaches or suggests the claimed limitations having a method of fabricating a semiconductor device by ion implanting to provide a SiC substrate at a surface with a region having dopant introduced therein, comprising the steps of providing a substrate with a mask layer including a polyimide resin film covered a first region, implanting ions to an implantation depth into the substrate at a second region of the surface of substrate free of the polyimide region film, wherein the polyimide resin film has a thickness of at least twice the implantation depth.

Claims 27, 29, 33-34: None of the references of record teaches or suggests the claimed limitations having a method of fabricating a semiconductor device comprising the steps of: a) providing a SiC substrate, b) providing a mask layer including a polyimide resin film that consists of a photosensitive polyimide resin on a first region of a surface of the substrate, by applying the polyimide resin film on the first region and a second region of the surface, then exposing the polyimide resin film to light at the first region, and then removing the polyimide resin film at the second region, wherein the step (b) does not involve photolithography employing a photoresist, c) heating the substrate to at least 300 oC and d) implanting ions while heating the substrate wherein the method does not involve chemical vapor deposition and does not involve dry etching.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably 10/528,440

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accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance".

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thao P. Le whose telephone number is 571-272-1785. The examiner can normally be reached on M-F (8-6).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor Steven H. Loke can be reached on 571-272-1657. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

/Thao Le/ Thao P. Le Primary Examiner December 4, 2007.